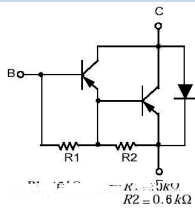


Rev. H Oct.-2018

Silicon PNP transistor in a TO-220 Plastic Package.

Complement to TIP112.

Medium power linear switching applications.

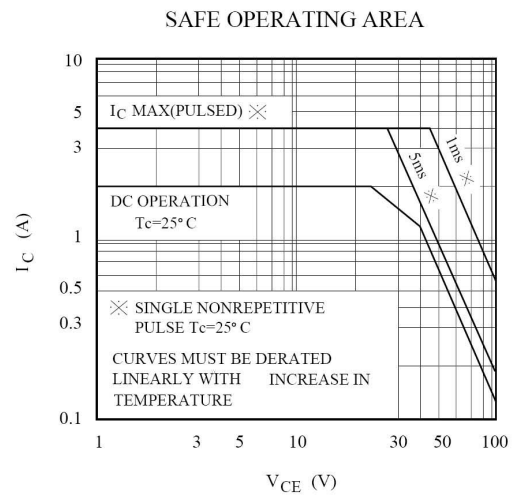
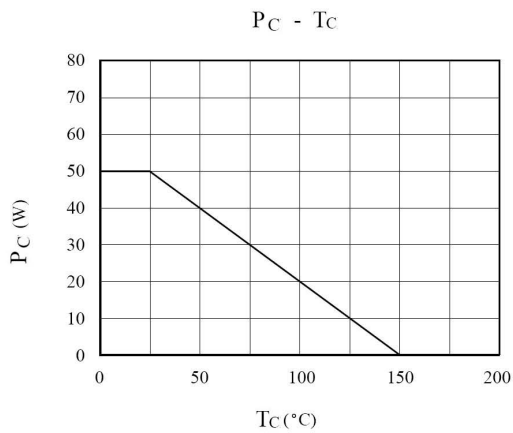
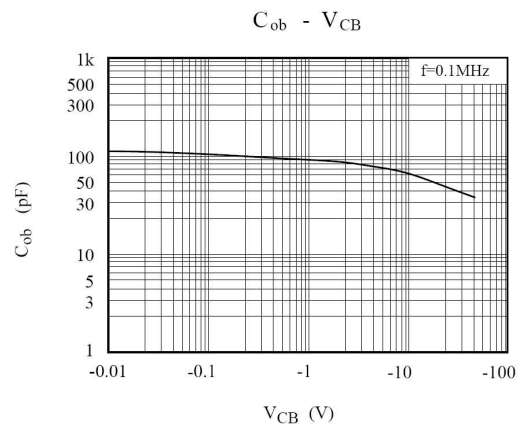
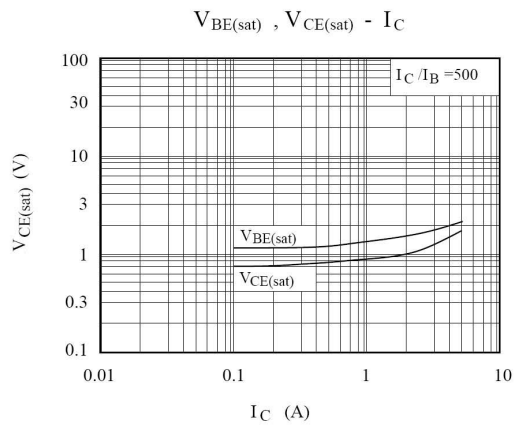
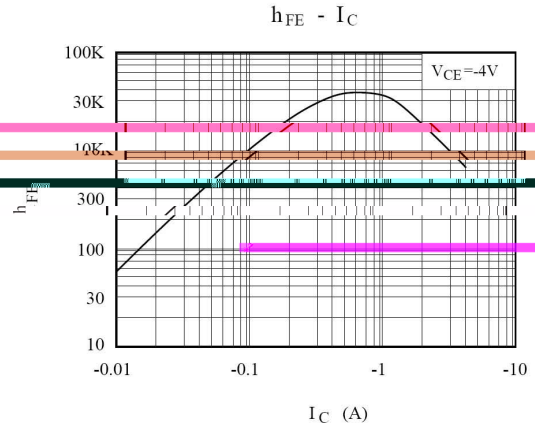
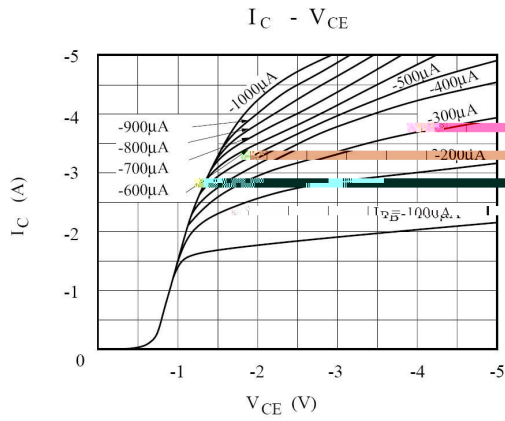


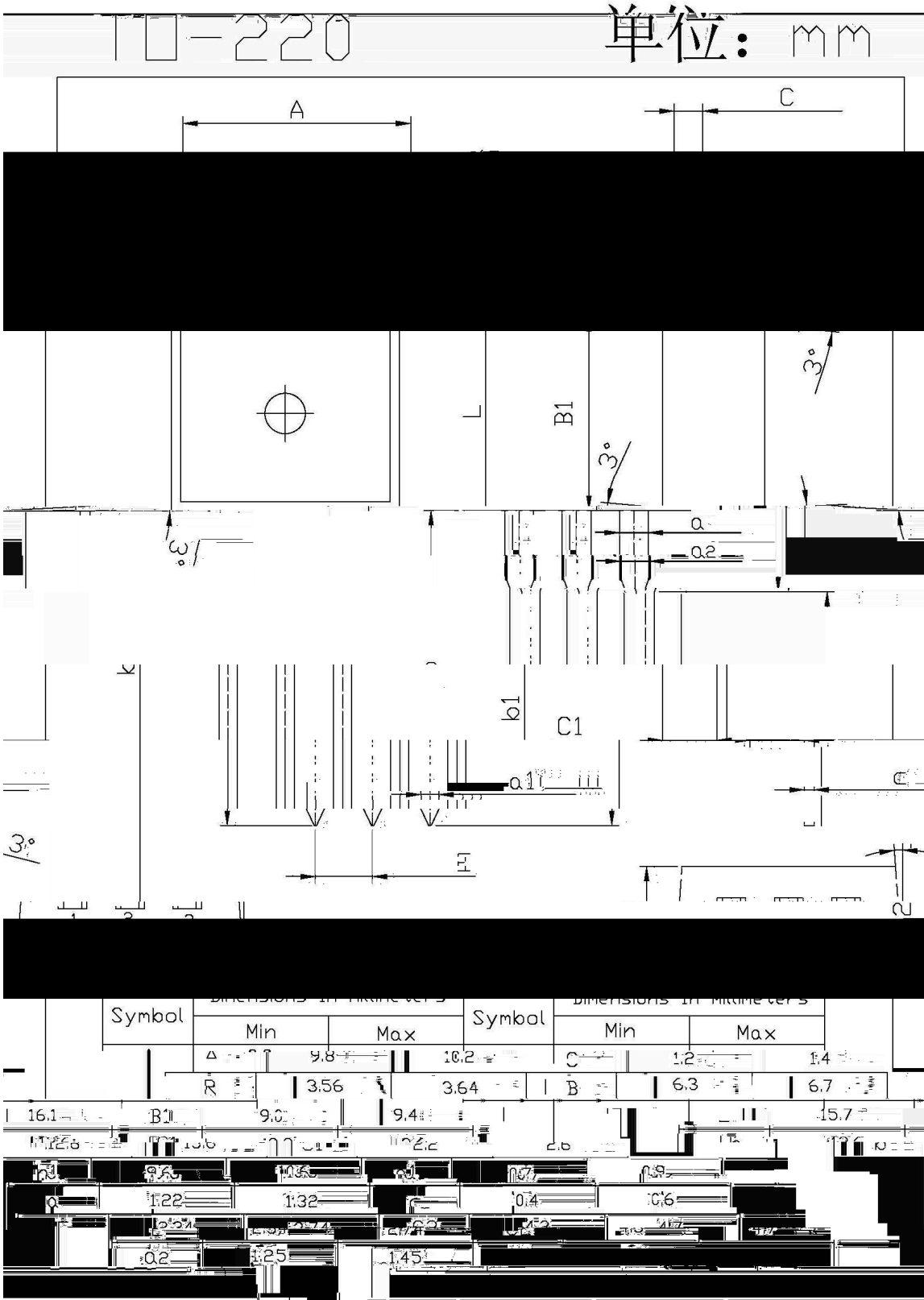
PIN1 Base PIN 2 Collector PIN 3 Emitter

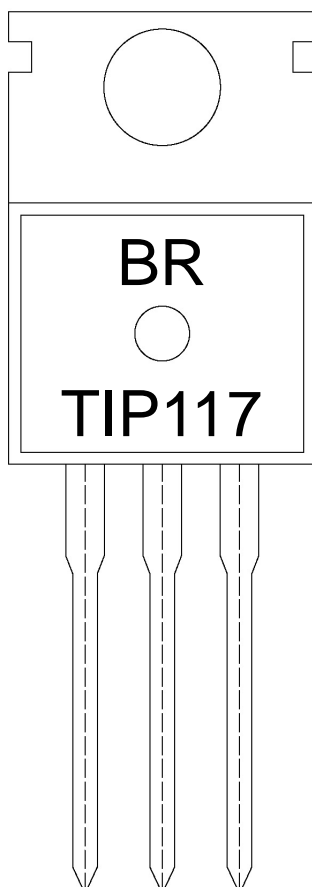
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Peak Collector Current	I_{CP}	-4.0	A
Base Current - Continuous	I_B	-50	mA
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	50	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-30\text{mA}$ $I_B=0$	-100			V
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-50\text{V}$ $I_B=0$			-2.0	mA
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-100\text{V}$ $I_E=0$			-1.0	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5\text{V}$ $I_C=0$			-2.0	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-4\text{V}$ $I_C=-1\text{A}$	1000			
	$h_{FE(2)}$	$V_{CE}=-4\text{V}$ $I_C=-2\text{A}$	500			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2\text{A}$ $I_B=-8\text{mA}$			-2.5	V
Base to Emitter On Voltage	$V_{BE(on)}$	$I_C=-2\text{A}$ $V_{CE}=-4\text{V}$			-2.8	V
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}$ $I_E=0$ $f=0.1\text{MHz}$			200	pF





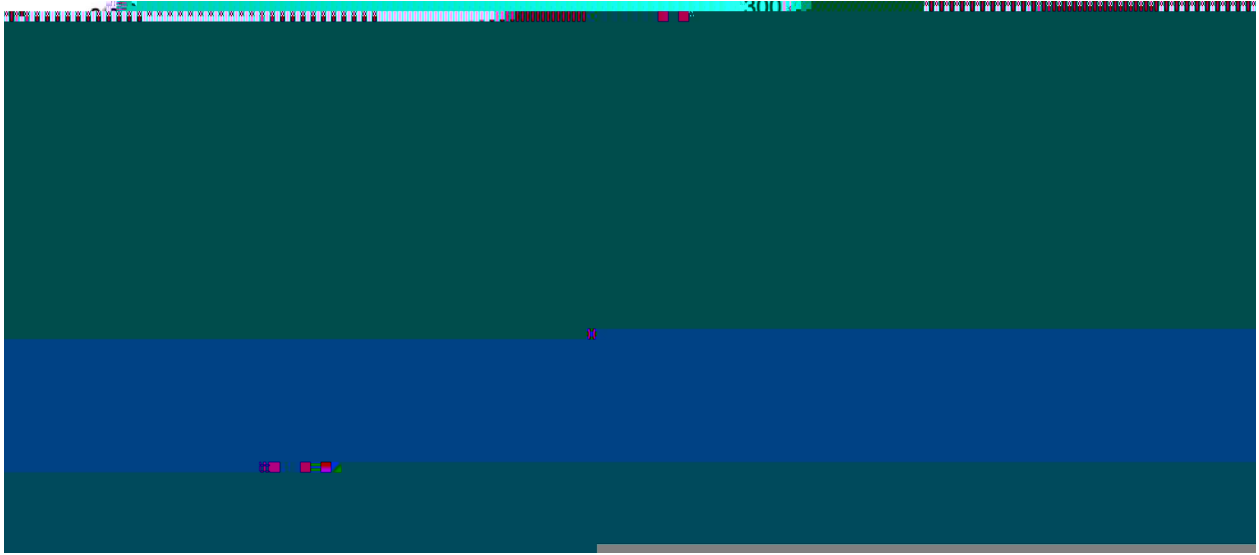


Note:

BR: Company Code

TIP117: Product Type.

***: Lot No. Code, code change with Lot No.



- | | |
|--|---|
| 1 25 150 60 90sec;
2 255 5 5 0.5sec;
3 2 10 /sec. | Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255 5 , Duration:5 0.5sec.
3. Cooling Speed: 2~10 /sec. |
|--|---|

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ BULK

Package Type	Units					Dimension (unit mm ³)		

/ TUBE

Package Type	Units					Dimension (unit mm ³)		